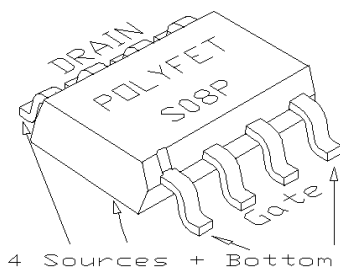




General Description

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"Polyfet"TM process features low feedback and output capacitances resulting in high F_t transistors with high input impedance and high efficiency.



SILICON GATE ENHANCEMENT MODE

RF POWER LDMOS TRANSISTOR

7.0 Watts Single Ended

Package Style S08 P

HIGH EFFICIENCY, LINEAR

HIGH GAIN, LOW NOISE

ABSOLUTE MAXIMUM RATINGS (T = 25 °C)

Total Device Dissipation	Junction to Case Thermal Resistance	Maximum Junction Temperature	Storage Temperature	DC Drain Current	Drain to Gate Voltage	Drain to Source Voltage	Gate to Source Voltage
60 Watts	2.50 °C/W	150 °C	-65 °C to 150 °C	8.0 A	36 V	36 V	20 V

RF CHARACTERISTICS (7.0 WATTS OUTPUT)

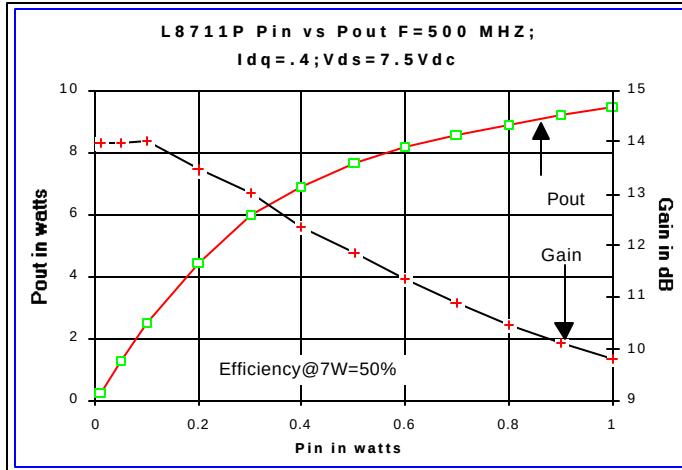
SYMBOL	PARAMETER	MIN	TYP	MAX	UNITS	TEST CONDITIONS
Gps	Common Source Power Gain	10			dB	Idq = 0.40 A, Vds = 7.5 V, F = 500 MHz
η	Drain Efficiency		50		%	Idq = 0.40 A, Vds = 7.5 V, F = 500 MHz
VSWR	Load Mismatch Tolerance			20:1	Relative	Idq = 0.40 A, Vds = 7.5 V, F = 500 MHz

ELECTRICAL CHARACTERISTICS (EACH SIDE)

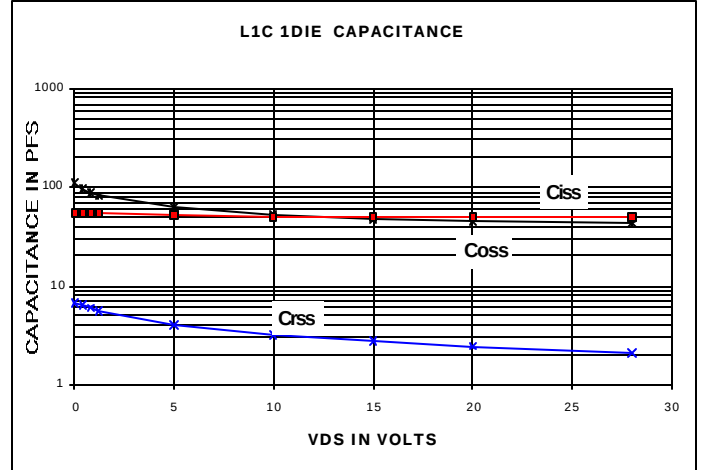
SYMBOL	PARAMETER	MIN	TYP	MAX	UNITS	TEST CONDITIONS
Bvdss	Drain Breakdown Voltage	36			V	Ids = 0.20 mA, Vgs = 0V
Idss	Zero Bias Drain Current			2.0	mA	Vds = 7.5 V, Vgs = 0V
Igss	Gate Leakage Current			1	uA	Vds = 0V Vgs = 30V
Vgs	Gate Bias for Drain Current	1		7	V	Ids = 0.20 A, Vgs = Vds
gM	Forward Transconductance		1.7		Mho	Vds = 10V, Vgs = 5V
Rdson	Saturation Resistance		0.40		Ohm	Vgs = 20V, Ids = 8.00 A
Idsat	Saturation Current		13.00		Amp	Vgs = 20V, Vds = 10V
Ciss	Common Source Input Capacitance		50.0		pF	Vds = 7.5 Vgs = 0V, F = 1 MHz
Crss	Common Source Feedback Capacitance		2.0		pF	Vds = 7.5 Vgs = 0V, F = 1 MHz
Coss	Common Source Output Capacitance		40.0		pF	Vds = 7.5 Vgs = 0V, F = 1 MHz

L8711P

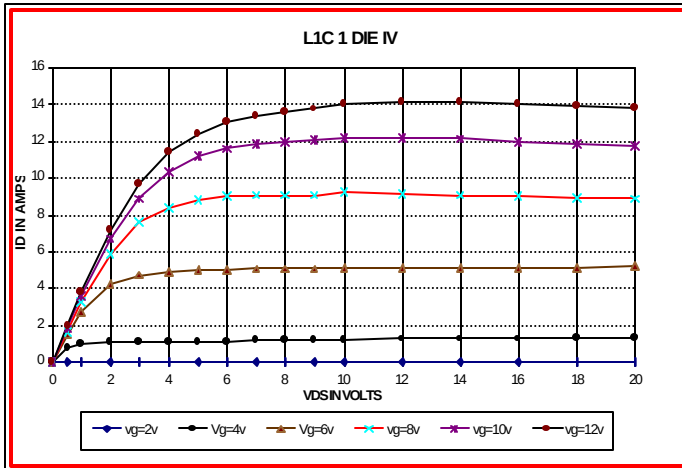
POUT VS PIN GRAPH



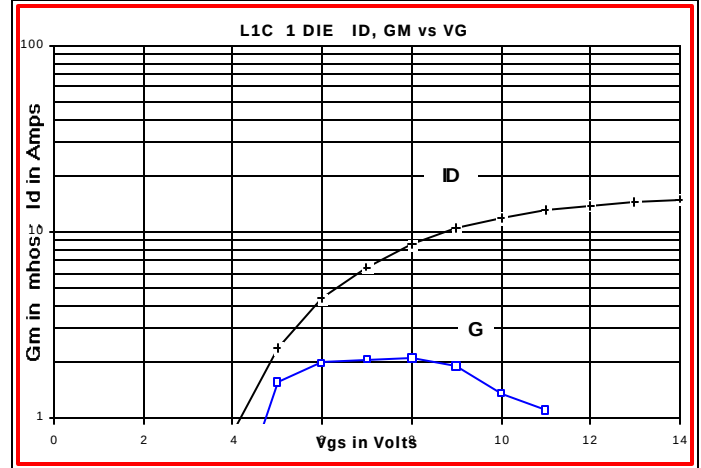
CAPACITANCE VS VOLTAGE



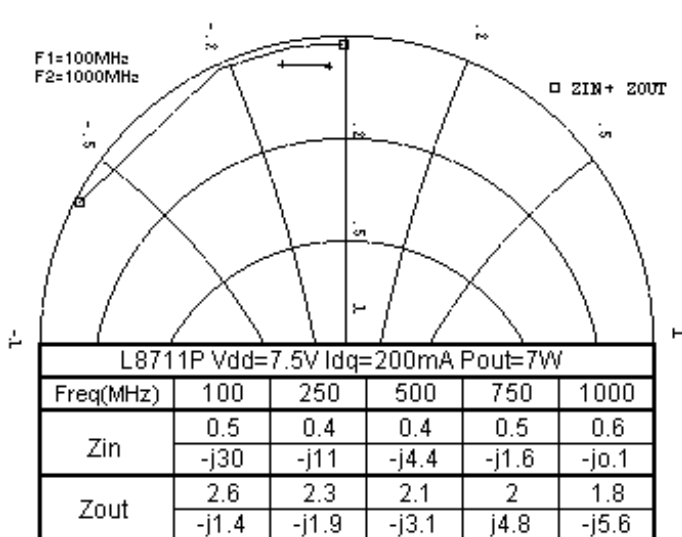
IV CURVE



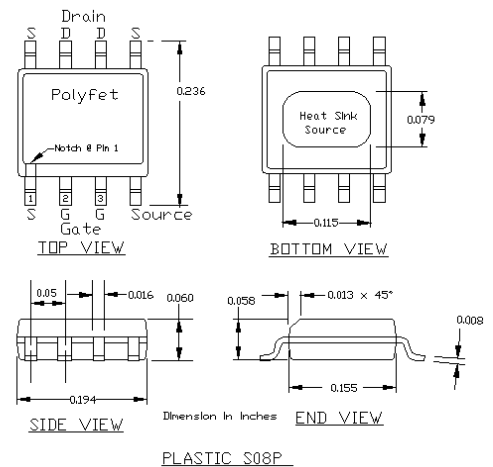
ID & GM VS VGS



Zin Zout



PACKAGE DIMENSIONS IN INCHES



Tolerance .XX +/- 0.01 .XXX +/- .005 inches

03/13/2002

POLYFET RF DEVICES

REVISION

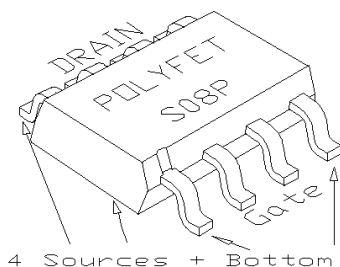
1110 Avenida Acaso, Camarillo, Ca 93012 Tel:(805) 484-4210 FAX: (805) 484-3393 EMAIL:Sales@polyfet.com URL:www.polyfet.com



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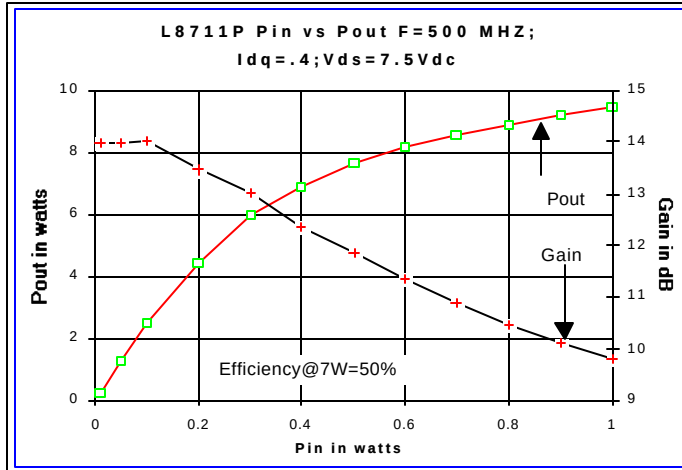
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ELECTRICAL CHARACTERISTICS (EACH SIDE)

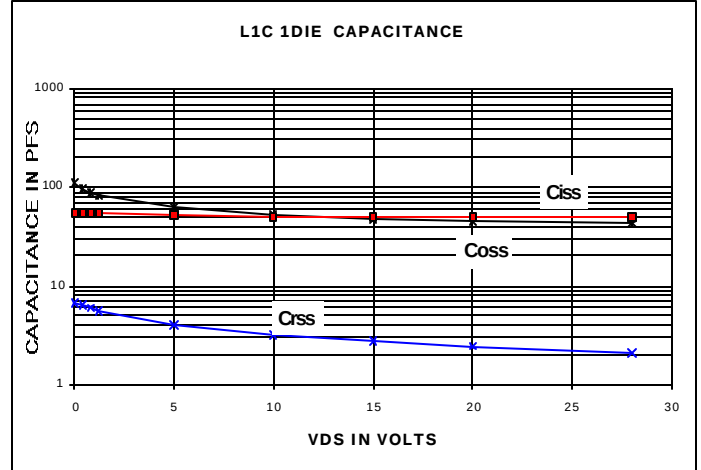
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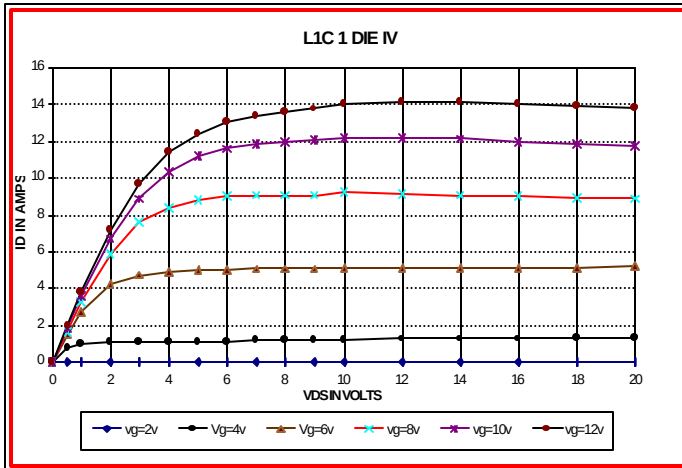
POUT VS PIN GRAPH



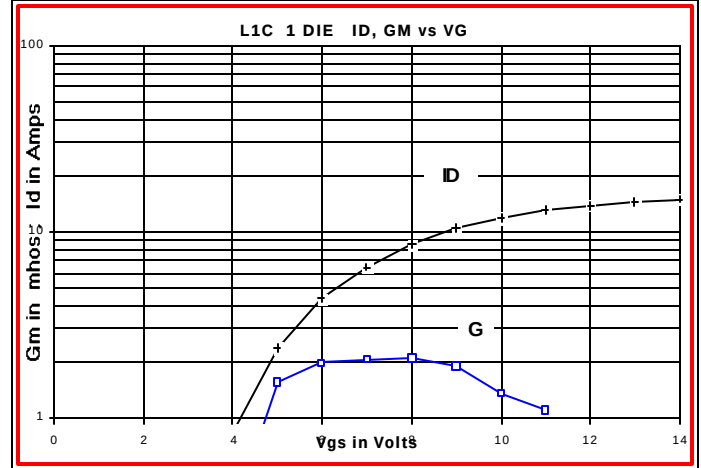
CAPACITANCE VS VOLTAGE



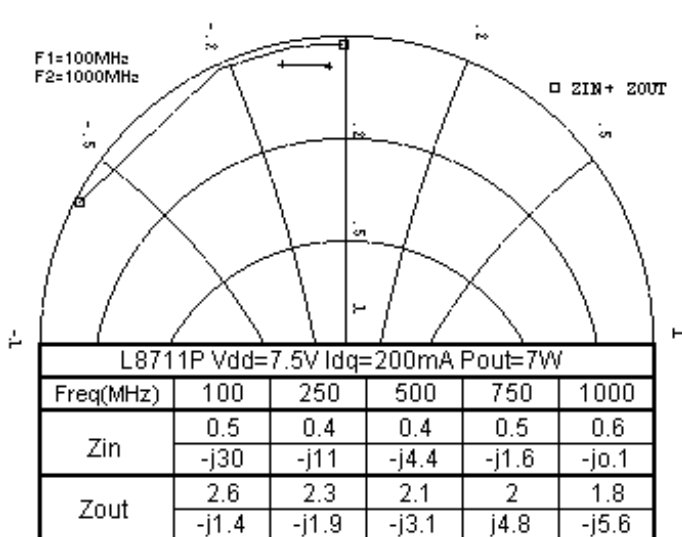
IV CURVE



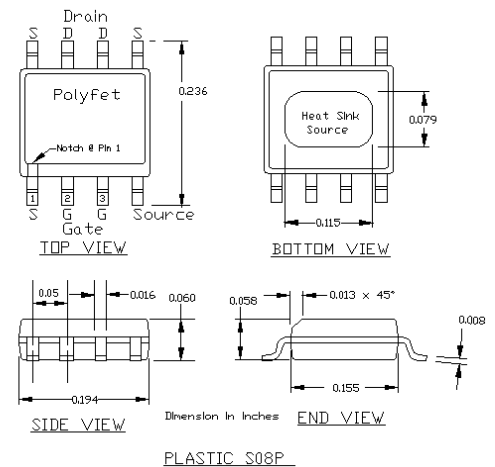
ID & GM VS VGS



Zin Zout



PACKAGE DIMENSIONS IN INCHES



Tolerance .XX +/- 0.01 .XXX +/- .005 inches

12/12/2001

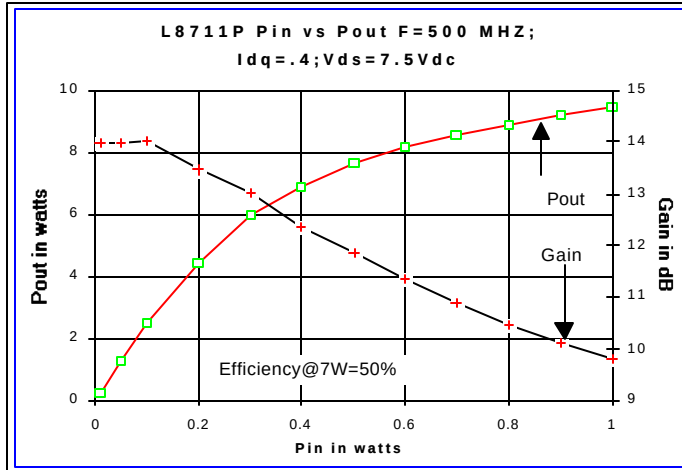
POLYFET RF DEVICES

REVISION

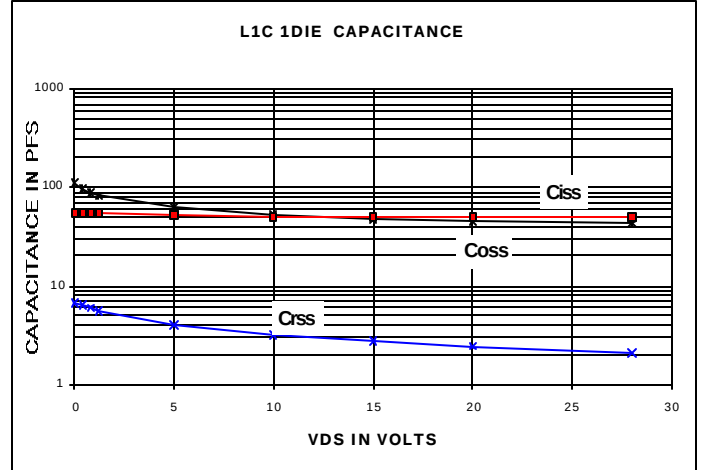
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L8711P

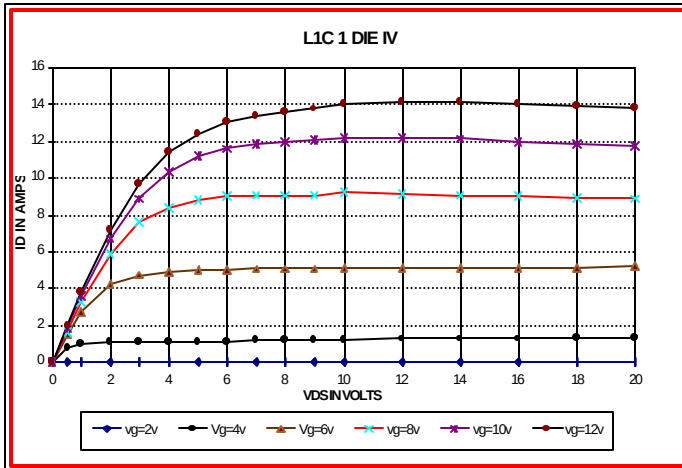
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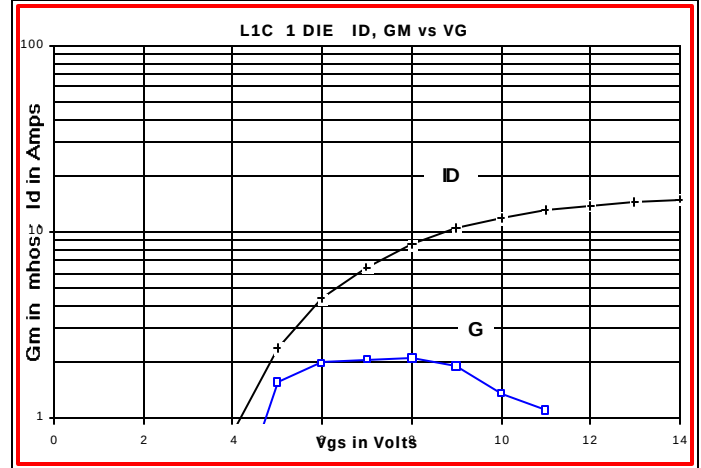
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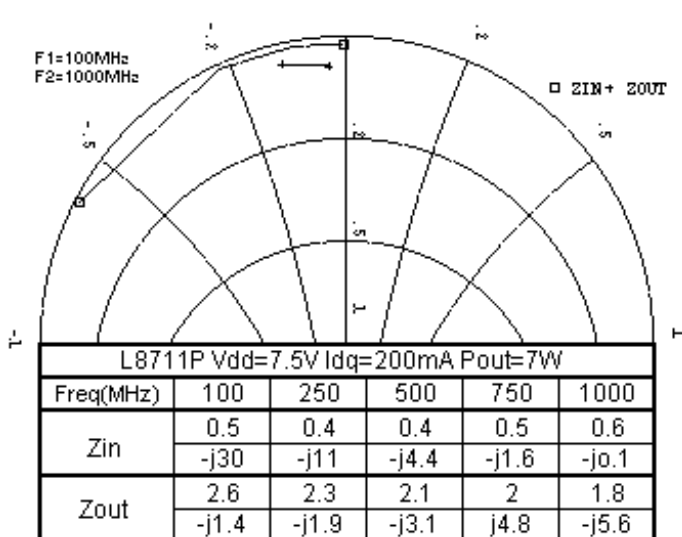
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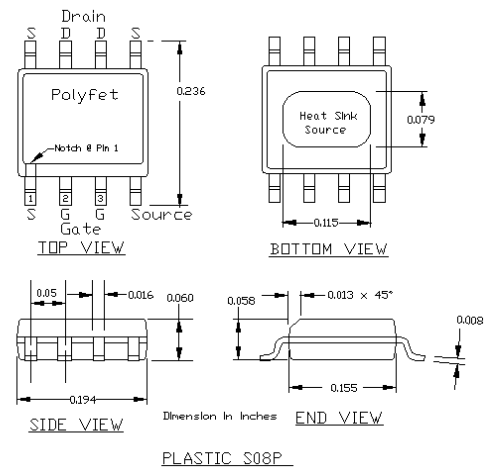
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